IN THE CLAIMS:

Claims 1-18 (Canceled).

Claim 19 (Original). A method of reworking an alignment film of a liquid crystal display device, comprising the steps of:

forming an organic protective film on a substrate;

forming a silicon nitride layer having a first etch rate on the organic protective film;

forming a first alignment film on the silicon nitride layer;

detecting at least one irregularity of the first alignment film formed on the silicon nitride layer;

eliminating the first alignment film with a second etch rate different from the first etch rate of the silicon nitride layer; and

forming a second alignment film on the silicon nitride layer.

Claim 20 (Original). The method of according to claim 19, wherein the step of eliminating the first alignment film includes dry-etching during rework processing.

Claim 21 (Original). The method according to claim 20, wherein the dry-etching is carried out by using at least one compound gas of SF_6, O_2, O_2+Cl_2, and CF_4.

Claim 22 (Original). The method according to claim 21, wherein a ratio of the compound gas is at least about SF_6:O_2=1:50.

Claim 23 (Original). The method according to claim 21, wherein a ratio of the compound gas is at least about SF_6:O_2=1:70.

Claim 24 (Original). The method according to claim 21, wherein the dry-etching includes a radio frequency power of about 500-1500W.

Claim 25 (Original). The method according to claim 19, wherein the silicon nitride layer includes hydrogen.

Claim 26 (Original). The method according to claim 19, further including the steps of:

forming a gate line and a gate electrode on the substrate;

forming a gate insulating film on the gate line, the gate electrode and the substrate;

forming a semiconductor layer on the gate insulating film; and

forming a data line, a source electrode and a drain electrode on the gate insulating film.

Claim 27 (Original). The method according to claim 26, further including the step of forming a pixel electrode on the silicon nitride layer to overlap at least one of the data line and the gate line.